



SYNSEMI SEMICONDUCTOR

1N5400G thru 1N5408G

3.0 Amps. Glass Passivated Junction Rectifiers
Voltage Range 50 to 1000 Volts Forward Current 3.0 Amperes

Features

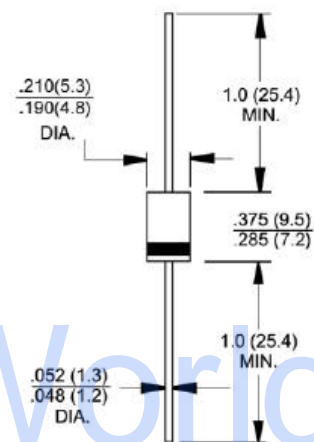
- ◆ Low forward voltage drop
- ◆ High current capability
- ◆ High reliability
- ◆ High surge current capability



DO-201AD

Mechanical Data

- ◆ Case: Molded plastic DO-201AD
- ◆ Epoxy: UL 94V-0 rate flame retardant
- ◆ Lead: Axial leads, solderable per MIL-STD-202, Method 208 guaranteed
- ◆ Polarity: Color band denotes cathode end
- ◆ High temperature soldering guaranteed: 250°C/10 seconds .375" (9.5mm) lead lengths at 5 lbs., (2.3kg) tension
- ◆ Weight: 0.042 ounce, 1.195 grams



Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Parameter	Symbols	1N 5400G	1N 5401G	1N 5402G	1N 5404G	1N 5406G	1N 5407G	1N 5408G	Units
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	Volts
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	Volts
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	Volts
Maximum average forward rectified current 0.375" (9.5mm) lead length @ $T_a=75^\circ\text{C}$	$I_{(AV)}$	3.0							Amps
Peak forward surge current, 8.3 ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	125.0							Amps
Maximum instantaneous forward voltage @ 3.0A	V_F	1.1							Volts
Maximum DC reverse current @ $T_a=25^\circ\text{C}$ at rated DC blocking voltage @ $T_a=125^\circ\text{C}$	I_R	5.0 100							μA
Typical junction capacitance (Note 1)	C_j	30							pF
Operating and storage temperature range	T_J, T_{STG}	-65 to +150							$^\circ\text{C}$

Notes: 1. Measured at 1 MHz and Applied Reverse Voltage of 4.0 V D.C.

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RATINGS AND CHARACTERISTIC CURVES

($T_a = 25^\circ\text{C}$ unless otherwise noted)

